

NCE N-Channel Enhancement Mode Power MOSFET



The NCE3095K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. **General Features**

V_{DS} = 30V, I_D = 95A

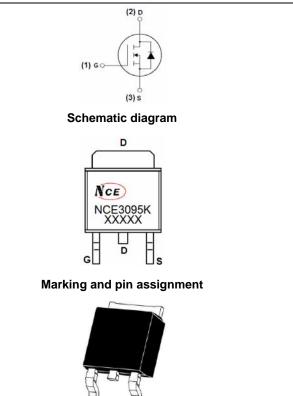
 $R_{DS(ON)} < 5.1 m\Omega @ V_{GS} = 10V$

- $R_{DS(ON)} < 8.5m\Omega @ V_{GS}=5V$
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3095K	NCE3095K	TO-252-2L	-	-	-

Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	95	A
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	67.2	A
Pulsed Drain Current	I _{DM}	300	A
Maximum Power Dissipation	PD	95	W
Derating factor		0.63	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	150	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.58	°C/W	1
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Electrical Characteristics (TC=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	30	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)	·	·					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$,I _D =250µA	1	1.5	2.2	V	
Drain Course On Chota Desintance	5	V _{GS} =10V, I _D =20A	-	4.1	5.1	mΩ	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =15A	-	5.5	8.5		
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A	30	-	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}		-	1784	-	PF	
Output Capacitance	C _{oss}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	266	-	PF	
Reverse Transfer Capacitance	C _{rss}		-	212	-	PF	
Switching Characteristics (Note 4)		·	-				
Turn-on Delay Time	t _{d(on)}		-	7	-	nS	
Turn-on Rise Time	tr	V_{DD} =5V,I _D =20A	-	6	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =6 Ω	-	30	-	nS	
Turn-Off Fall Time	t _f		-	8	-	nS	
Total Gate Charge	Qg)/ _15)/ _20A	-	38.4	-	nC	
Gate-Source Charge	Q _{gs}	V _{DS} =15V,I _D =20A, V _{GS} =10V	-	5.8	-	nC	
Gate-Drain Charge	Q _{gd}	V _{GS} -10V	-	7.9	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	0.85	1.2	V	
Diode Forward Current (Note 2)	I _S		-	-	95	А	
Reverse Recovery Time	t _{rr}	TJ = 25°C, I _F = 20A	-	-	47	nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	-	25	nC	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LE				y LS+LD)	

Notes:

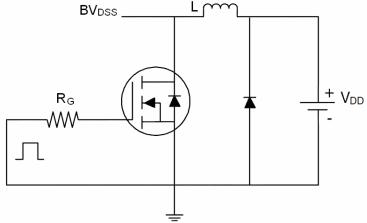
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}$ C,V_{DD}=15V,V_G=10V,L=0.5mH,Rg=25 Ω



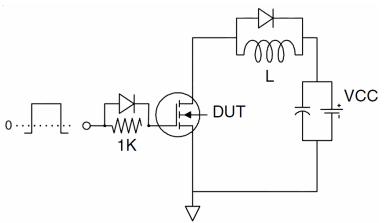
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Test Circuit

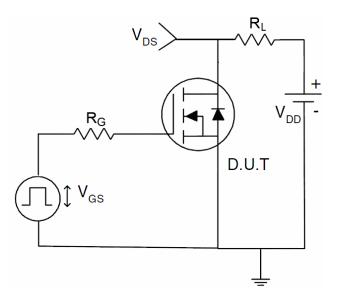
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit

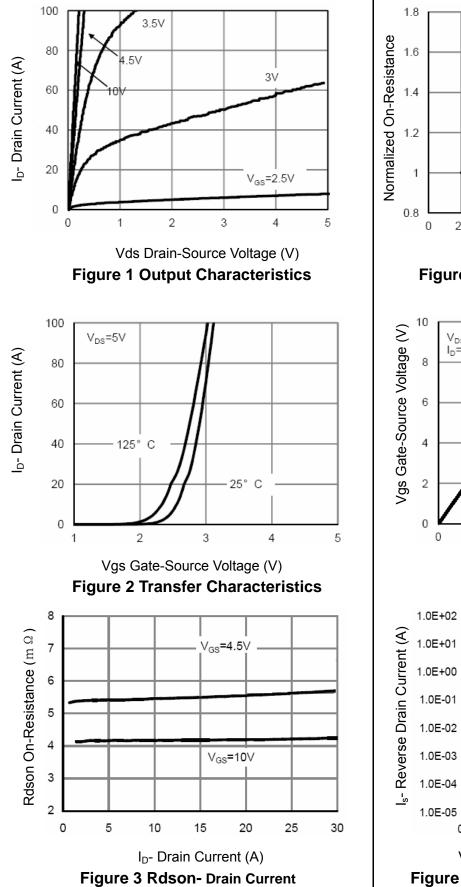


3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)



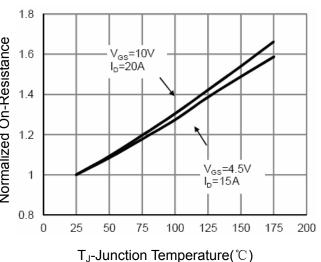
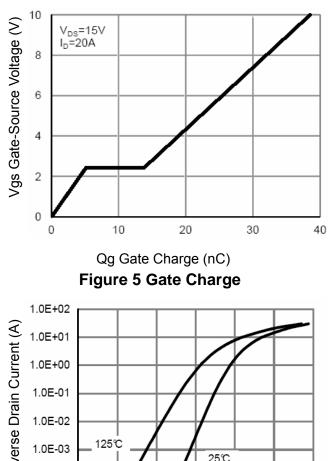
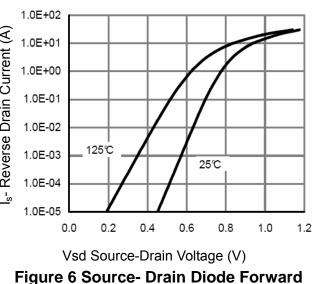


Figure 4 Rdson-Junction Temperature

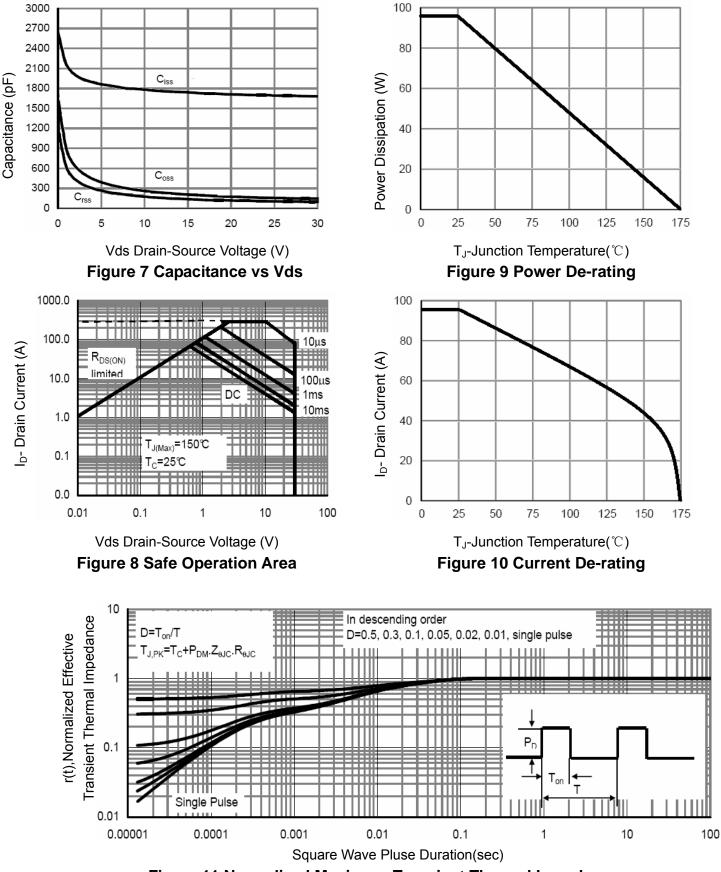


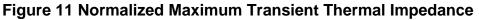




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NCE3095K

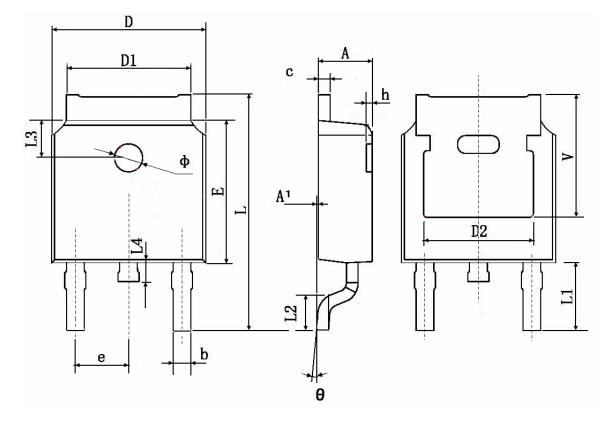






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TO-252 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.8	330 TYP.	0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.90	0 TYP.	0.114	TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.60	0 TYP.	0.063	B TYP.	
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.35	0 TYP.	0.211 TYP.		



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